

QUANTUM AND SOLID STATE PHYSICS : ASSIGNMENT

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AAKASH JOG
ID : 989323563

Exercise 1.

If we require a silicon sample to have an electron concentration 4 times higher than its hole concentration, i.e. $n = 4p$, which of the following dopant concentration would you choose, expressed in terms of intrinsic carrier concentration n_i ?

- (1) $N_D = 0.5n_i$
- (2) $N_D = 2n_i$
- (3) $N_D = 1.5n_i$
- (4) $N_A = 0.5n_i$
- (5) $N_A = 2n_i$
- (6) $N_A = 1.5n_i$

Solution 1.

As the requirement is to have an electron concentration higher than the original sample, the dopant must be a donor.

For the original sample,

$$np = n_i^2$$

Therefore, for the doped sample,

$$4pn = N_D^2$$
$$\therefore 4n_i^2 = N_D^2$$

Therefore,

$$N_D = 2n_i$$

Hence, the dopant concentration should be (2) $N_D = 2n_i$.

Exercise 2.

Let's examine 3 wafers, all of which are doped with a concentration of 10^{15} dopants cm^{-3} .

- (1) Wafer A: Silicon, in which the dopant energy level is 1.095 eV above the valence energy level E_V .
- (2) Wafer B: Silicon, in which the dopant energy level is 1.08 eV above the valence energy level E_V .
- (3) Wafer C: GaAs, in which the dopant energy level is 1.095 eV above the valence energy level E_V .

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- (1) Do we expect the dopants in wafers A, B, and C to be donors or acceptors? Draw the energy diagrams for each wafer, and clearly label all relevant energy levels and spacing between them.
- (2) As the temperature is increased, which wafer will be the first to transition from the ionization region to the extrinsic region?
- (3) For which wafer will intrinsic carriers start to dominate at the lowest temperature?

Solution 2.

- (1) As the dopant energy in the wafers is closer to E_C , than E_V , the dopants will be donors.

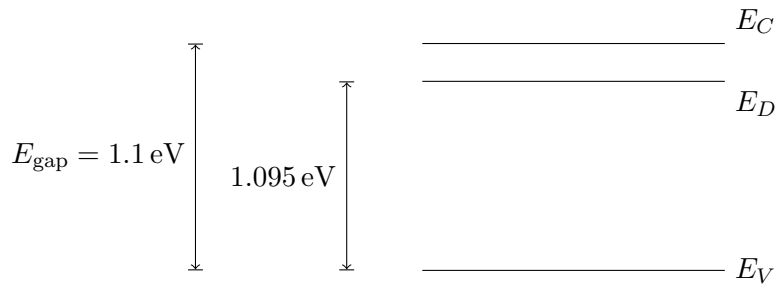


FIGURE 1. Energy Diagram: Wafer A

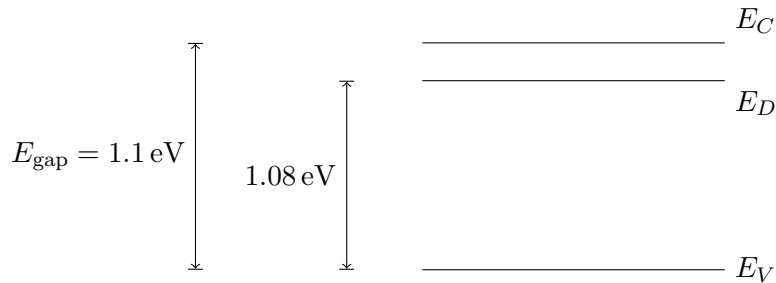


FIGURE 2. Energy Diagram: Wafer B

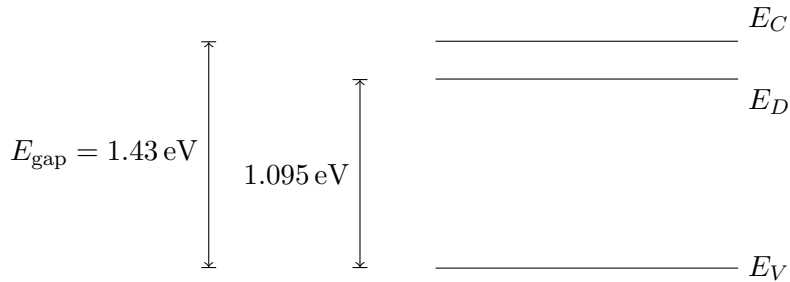


FIGURE 3. Energy Diagram: Wafer C

- (2) When the temperature is increased, the wafer for which the gap between E_D and E_C is the least will be the first to transition into the extrinsic region. Therefore, wafer A will be the first to transition.
- (3) The energy band gap of Si is less than that of GaAs. However, in wafer B, the dopant charge carriers are at a lower energy level than that of those in wafer A. Hence, the intrinsic carriers in wafer B will start to dominate at the lowest temperature.

Exercise 3.

Two wafers of silicon are doped with the following concentration

$$N_{D1} = 10^{15} \text{cm}^{-3}$$

$$N_{D2} = 10^{16} \text{cm}^{-3}$$

Is it possible that the electron concentration n in both wafers is identical, i.e. $n_1 = n_2$?

- (1) No
- (2) Yes, in the extrinsic region
- (3) Yes, in the intrinsic region
- (4) Yes, in both the extrinsic and intrinsic regions

Solution 3.

$$n = N_D + \text{number of thermally generated EHPs}$$

Therefore,

$$n_1 = N_{D1} + \text{number of thermally generated EHPs}$$

$$n_2 = N_{D2} + \text{number of thermally generated EHPs}$$

Therefore,

$$n_1 \neq n_2$$

Therefore, it is not possible for the electron concentration in both wafers to be identical.

Exercise 4.

A particle is represented, at time $t = 0$, by the following wave function.

$$\psi(x, 0) = \begin{cases} A \frac{x}{a} & ; \quad 0 \leq x \leq a \\ A \frac{b-x}{b-a} & ; \quad a \leq x \leq b \\ 0 & ; \quad \text{otherwise} \end{cases}$$

- (1) Determine the normalization constant A .
- (2) Sketch $\psi(x, 0)$ as a function of x .
- (3) Where is the particle most likely to be found at $t = 0$?
- (4) What is the probability of finding the particle to the left of a ?
- (5) What is the expectation value of x , at time $t = 0$?

Solution 4.

(1)

$$\begin{aligned}
1 &= \int_{-\infty}^{\infty} |\psi(x, 0)|^2 dx \\
&= \int_0^a A^2 \frac{x^2}{a^2} dx + \int_a^b A^2 \frac{(b-x)^2}{(b-a)^2} dx \\
&= \frac{A^2}{a^2} \frac{x^3}{3} \Big|_0^a + \frac{A^2}{(b-a)^2} \left(b^2 x - bx^2 + \frac{x^3}{3} \right) \Big|_a^b \\
&= \frac{A^2}{a^2} \frac{a^3}{3} + \frac{A^2}{(b-a)^2} \left(b^3 - b^3 + \frac{b^3}{3} - ab^2 + a^2b - \frac{a^3}{3} \right) \\
&= \frac{A^2 a}{3} + \frac{A^2}{(b-a)^2} \left(\frac{b^3}{3} - ab^2 + a^2b - \frac{a^3}{3} \right) \\
&= A^2 \left(\frac{a}{3} + \frac{b^3}{3(b-a)^2} - \frac{ab^2}{(b-a)^2} + \frac{a^2b}{(b-a)^2} - \frac{a^3}{3(b-a)^2} \right) \\
&= A^2 \left(\frac{a(b-a)^2 + b^3 - 3ab^2 + 3a^2b - a^3}{3(b-a)^2} \right) \\
&= A^2 \left(\frac{b(b-a)^2}{3(b-a)^2} \right) \\
&= \frac{A^2 b}{3}
\end{aligned}$$

Therefore,

$$A = \sqrt{\frac{3}{b}}$$

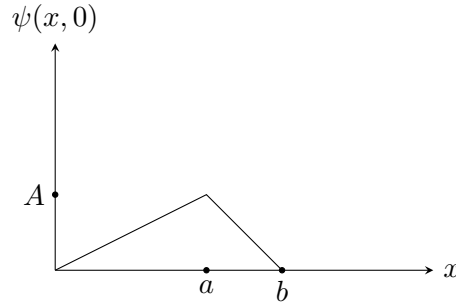
(2)

$$A = \sqrt{\frac{3}{b}}$$

Therefore,

$$\psi(x, 0) = \begin{cases} \sqrt{\frac{3}{b}} \frac{x}{a} & ; \quad 0 \leq x \leq a \\ \sqrt{\frac{3}{b}} \frac{b-x}{b-a} & ; \quad a \leq x \leq b \\ 0 & ; \quad \text{otherwise} \end{cases}$$

Therefore,



- (3) As the value of $|\psi(x)|^2$ is maximum at $x = a$, the particle is most likely to be found at $x = a$.
- (4) The probability of finding the particle at to the left of a is

$$\begin{aligned} \int_0^a |\psi(x, 0)|^2 dx &= \int_0^a \frac{3x^2}{ba^2} dx \\ &= \frac{x^3}{a^2b} \Big|_0^a \\ &= \frac{a}{b} \end{aligned}$$

(5)

$$\begin{aligned} \langle x \rangle &= \int_{-\infty}^{\infty} x |\psi(x)|^2 dx \\ &= \int_0^a x \left(\frac{A^2 x^2}{a^2} \right) dx + \int_a^b x \frac{A^2 (b-x)^2}{(b-a)^2} dx \\ &= \frac{1}{4b} (6a^2 - 2ab - b^2) \end{aligned}$$

Exercise 5.

A particle is represented, at time $t = 0$, by the following wave function.

$$\psi(x, 0) = \begin{cases} A(a^2 - x^2) & ; \quad -a \leq x \leq a \\ 0 & ; \quad \text{otherwise} \end{cases}$$

- (1) Determine the normalization constant A .
- (2) What is the expectation value of x , at time $t = 0$?
- (3) What is the expectation value of p , at time $t = 0$? Can you answer this part based on Ehrenfest's theorem? Explain your answer
- (4) What is the expectation value of x^2 , at time $t = 0$?
- (5) What is the expectation value of p^2 , at time $t = 0$?

Solution 5.

(1)

$$\begin{aligned}
1 &= \int_{-\infty}^{\infty} |\psi(x, 0)|^2 dx \\
&= \int_{-a}^a A^2 (a^2 - x^2) dx \\
&= \frac{16a^2}{15A^2}
\end{aligned}$$

Therefore,

$$A^2 = \frac{15}{16a^2}$$

Therefore,

$$A = \sqrt{\frac{15}{16a^2}}$$

(2)

$$\begin{aligned}
\langle x \rangle &= \int_{-a}^a x |\psi(x, 0)|^2 dx \\
&= \int_{-a}^a x A^2 (a^2 - x^2)^2 dx
\end{aligned}$$

As the function is odd, and the interval is symmetric across the origin, the integral is zero.

Therefore,

$$\langle x \rangle = 0$$

(3) By Ehrenfest's theorem,

$$\begin{aligned}
\langle p \rangle &= m \langle v \rangle \\
&= m \frac{d\langle x \rangle}{dt} \\
&= 0
\end{aligned}$$

(4)

$$\begin{aligned}
\langle x^2 \rangle &= \int_{-a}^a x^2 |\psi(x, 0)|^2 dx \\
&= \int_{-a}^a x^2 A^2 (a^2 - x^2)^2 dx \\
&= 2 \int_0^a x^2 A^2 (a^2 - x^2)^2 dx \\
&= \frac{a^2}{7}
\end{aligned}$$

(5)

$$\begin{aligned}
\langle p^2 \rangle &= \int_{-a}^a \psi^*(x, 0) \left(-\hbar^2 \right) \frac{\partial^2}{\partial x^2} \psi(x, 0) dx \\
&= \int_{-a}^a A (a^2 - x^2) \left(-\hbar^2 \right) \frac{\partial^2}{\partial x^2} A (a^2 - x^2) dx \\
&= \frac{5\hbar^2}{2a^2}
\end{aligned}$$